

REMARKS

Claims 16 and 18-34, as amended, remain herein. Claims 3-8 and 12-15 also remain herein but are presently withdrawn from consideration. Claims 1-2, 9-11 have been cancelled without prejudice. New claims 21-34 have been added. Support for the new claims may be found throughout the specification (see, e.g., original claims and Example 2 at page 46, and Example 8 at page 56 of the specification). The specification has been amended to correct an error in translation.

Claims 1, 2, 9-11, 16, and 18-20 were rejected under 35 U.S.C. §103(a) over Hosokawa et al. U.S. Patent 6,379,824 in view of Bach et al., "Determination of the ionization potentials of aluminum oxides via charge transfer," *J. Phys. Chem.* **1991**, 95, 9091-9094, in further view of Mishima JP 2002-056976.

Applicants' claim 21 recites an organic luminescence device including an insulating or semiconductive inorganic thin film layer having an energy gap of 2.7 eV or more; the inorganic thin film layer including one or more metals or compounds selected from metals, metal carbides, nitrides, silicides and borides.

Applicants' claim 22 recites an organic luminescence device including an insulating or semiconductive inorganic thin film layer having an energy gap of 2.7 eV or more; the inorganic thin film layer including one or more compounds selected from metal chalcogenides and oxynitrides; the metals being two or more metals including one or more metals selected from the following A group and one or more metals selected from the following B group:

A group: In, Sn, Ga, Si, Ge, Zn, Cd, Mg, Al, Ta and Ti;

B group: B, Tl, Ge, Sn, Pb, As, Bi, Te, Po, Au, Ni, Ir, Pt, Pd, Ru, Bi and Co.

Applicants' claim 23 recites an organic luminescence device including an insulating or semiconductive inorganic thin film layer having an energy gap of 2.7 eV or more; the inorganic thin film layer including germanium oxide or cerium oxide.

Hosokawa '824 does not teach or suggest applicants' organic luminescence device. Hosokawa '824 discloses the use of a semiconductor layer including an oxide or oxynitride of Ba, Ca, Sr, Yb, Al, Ga, In, Li, Na, Cd, Mg, Si, Ta, Sb and Zn (see Hosokawa '824 at column 3, lines 9-16). Hosokawa, however, says nothing about an organic luminescence device including an inorganic thin film layer including (1) one or more metals or compounds selected from metals, metal carbides, nitrides, silicides and borides; (2) one or more metal chalcogenides or oxynitrides, wherein the metal is selected from the following B group: B, Tl, Ge, Sn, Pb, As, Bi, Te, Po, Au, Ni, Ir, Pt, Pd, Ru, Bi and Co; or (3) germanium oxide or cerium oxide.

Neither Bach nor Mishima teaches or suggests what is missing from Hosokawa '824. Thus, neither Hosokawa '824, Bach, nor Mishima discloses all elements of applicants' claimed invention. Furthermore, Hosokawa '824, Bach, and Mishima disclose nothing that would have suggested applicants' claimed invention to one of ordinary skill in the art. There is no disclosure or teaching in Hosokawa '824, Bach, Mishima, or otherwise in this record, that would have suggested the desirability of modifying any portions thereof effectively to anticipate or suggest applicants' presently claimed invention.

Reconsideration and withdrawal of this rejection are respectfully requested.

Accordingly, this application is now fully in condition for allowance and a notice to that effect is respectfully requested. The PTO is hereby authorized to charge/credit any fee deficiencies or overpayments to Deposit Account No. 19-4293 (Order No. 28955.1044). If further amendments would place this application in even better condition for issue, the Examiner is invited to call applicants' undersigned attorney at the number listed below.

Respectfully submitted,

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